DOCUMENT CHANGE REQUEST

DCR number 304	Changes required for: General	Originator: S JEFFERY
Date: 2006/11/14	Date sent: 2006/11/14	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

Title:	Transistors Low Power PNP, based on type 2N4033		
Number:	5202/008	Issue:	1

Other documents affected:

Page:

Total re-write

Paragraph:

Total re-write

Original wording:

Proposed wording:

Total reformat of this Detail Specification (under Generic Specification No. 5000) as part of the ongoing conversion to the ESCC format. See below for summary of changes and attached Issue 2 Draft A of the Specification.

Note: known support for active procurement against this specification includes the following manufacturers:

STMICROELECTRONICS/F (ESCC QPL listed with qualified Variants 01, 02, 04 and 05)

Summary of changes to the current format, layout and content is as follows:

1. Rewording and restructure of various sections and paragraphs of the specification plus other editorial changes based on the layout and editorial content of other Detail Specifications already converted to ESCC format (e.g. changes described in DCR No. 203).
2. Deletion of any redundant paragraphs and information, e.g.: Mechanical Requirements.
3. Para. 1.7 High Temperature Test Precautions requirements moved to be a note in the Maximum Ratings table.
4. Deletion of obsolete lead finish D7 / Variant 03 from the available range (not supported by STM).
5. Maximum Ratings table: Power Dissipation ratings amended to include power dissipation at Tcase â.- 25Â°C.
6. Figure 1 Parameter Derating Information moved to be a note in the Maximum Ratings table.
7. Para. 4.3.2 Weight Requirements moved to Component Type Variants table.
8. Figure 2 re-named "Physical Dimensions and Terminal Identification"; Figure 2(a) amended to reflect the TO-39 package currently supplied. Notes revised, including addition of a terminal identification note.
9. Para. 4.3.3 Terminal Strength: Erroneous text "Applied Force: 2.5Â±0.1 Newtons" deleted.
10. Para. 4.4.1 Case requirements for Variants 01 and 02 corrected to reflect a TO-39 metal can.
11. Para. 4.4.2 Lead Material and Finish replaced by a reference to the Component Type Variants Para.
12. Delete requirement for marking of the test level letter from ESCC Component number as per latest ESCC No. 21700.

DOCUMENT CHANGE REQUEST

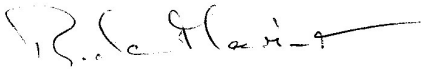
DCR number 304	Changes required for: General	Originator: S JEFFERY
Date: 2006/11/14	Date sent: 2006/11/14	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

13. Figure 3 (Functional Diagram): Note added to clarify that the lids of the CCP packaged devices are not connected to any terminal.
14. Table 2, Characteristic "D.C. Forward Current Transfer Ratio" has been changed to "Forward-Current Transfer Ratio".
15. Table 2, Characteristic "A.C. Forward Current Transfer Ratio" has been changed to "Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio", Symbol corrected to |hfe| (was hfe).
16. Table 2: Replace LTPD7 sampling for AC parameters tests (designated by "Note 2") with an equivalent fixed sample of 32 components with 0 failures (or 100%).
17. Table 2 and Figure 4: The Switching Times characteristics have been amended to reflect the new format.
18. Table 3 (High and Low Temperature Electrical Measurements): 100% inspection has been replaced by a sample of 5 components with 0 failures, or 100%, in line with the new Generic 5000 Issue 3.
19. Table 3, ICBO: Test Method corrected (was 3076, now 3036).
20. Table 3, Test Conditions: Standard tolerances have been added to the specified Tamb.
21. Table 4: Absolute limits have been added for information.
22. Tables 4 and 6, Characteristic "D.C. Forward Current Transfer Ratio 2" has been changed to "Forward-Current Transfer Ratio 2".
23. Tables 2, 3 and 4 - Test Conditions column: addition of Test, or Bias, Conditions for referenced MIL-STD-750 Test Methods as and where applicable.
24. Table 5 - Test Conditions for High Temperature Reverse Bias amended: Tamb was +150Â°C, now +150(+0 -5)Â°C; Duration was 48 hrs, now 48 hours minimum, in line with new Generic 5000 and MIL specifications.
25. Table 6: ICBO limit sense corrected (was 50nA, now â..50nA).
26. Appendix A for STM added:
a) To introduce a deviation to Special In-process Control Internal Visual Inspection for CCP packages. A sample radiographic inspection to verify the die attach process per STMicroelectronics procedure 0076637 may replace the standard inspection criteria.
b) To introduce a note about wafer level pilot lot testing in that AC characteristics during screening may be considered guaranteed but not tested. Note STM is an ESCC QPL listed manufacturer and this device is ESCC qualified; accordingly there is an ESCC approved PID for this device. This amendment is considered technically acceptable on this basis.

Justification:

(see also change details for each item above)

1. Part of the ongoing activity of conversion of cover-sheeted ESA/SCC specifications to the ESCC format.
2. To make the format and presentation consistent with the various other ESCC Detail Specifications already converted to ESCC format.
3. To make the content consistent with ESCC Generic Specification No. 5000 Issue 3.
4. To incorporate specific deviations requested by manufacturer STM within Appendix A which are considered technically acceptable (based on ESCC approved PID for this and other ESCC qualified components manufactured by STM).
5. Update manufacturersâ.. current product availability.
6. To make corrections to technical errors in the previous issue.
7. Standardisation of the TO-39 and CCP packages in all applicable ESCC detail specs.

Attachments:
5202008_Issue_2_-_Draft_A.pdf, null
Modifications:
N/A
Approval signature:

Date signed:
2006-11-14

TRANSISTORS, LOW POWER, PNP

BASED ON TYPE 2N4033

ESCC Detail Specification No. 5202/008

Issue 2 - Draft A	November 2006

Document Custodian: European Space Agency - see https://escies.org

LEGAL DISCLAIMER AND COPYRIGHT

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
187, TBD	Specification up issued to incorporate editorial and technical changes per DCR.

TABLE OF CONTENTS

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

(a) ESCC Generic Specification No. 5000
(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520200801

- Detail Specification Reference: 5202008
- Component Type Variant Number: 01 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
01	2N4033	TO-39	D2	1.2
02	2N4033	TO-39	D3 or D4	1.2
04	2N4033	CCP	2	0.06
05	2N4033	CCP	4	0.06

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

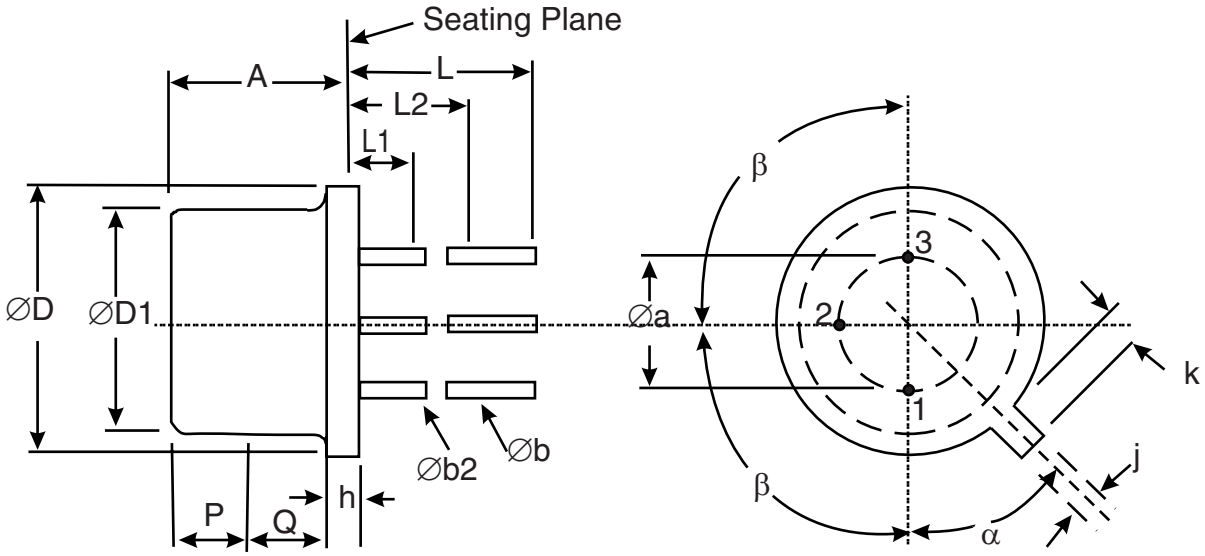
Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V_{CBO}	-80	V	Over entire operating temperature range
Collector-Emitter Voltage	V_{CEO}	-80	V	
Emitter-Base Voltage	V_{EBO}	-5	V	
Collector Current	I_C	1	A	Continuous
Power Dissipation For TO-39 For CCP	P_{tot1}	 800 500	mW	At $T_{amb} \leq +25^oC$ Note 1
For CCP	P_{tot2}	760 (Note 2)	mW	
For TO-39	P_{tot3}	800	mW	At $T_{case} \leq +25^oC$ Note 1
Operating Temperature Range	T_{op}	-65 to +200	^oC	Note 3
Storage Temperature Range	T_{stg}	-65 to +200	^oC	Note 3
Soldering Temperature For TO-39 For CCP	T_{sol}	 +260 +245	^oC	 Note 4 Note 5

NOTES:

1. For T_{amb} or $T_{case} > +25^oC$, derate linearly to 0W at $+200^oC$.
2. When mounted on a 15 x 15 x 0.6mm ceramic substrate.
3. For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^oC$ shall be carried out in a 100% inert atmosphere.
4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
5. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-39) - 3 lead



Symbols	Dimensions mm		Notes
	Min	Max	
Øa	4.83	5.35	
A	6	6.6	
Øb	0.4	0.533	2, 3
Øb2	0.4	0.483	2, 3
ØD	8.31	9.4	
ØD1	7.75	8.51	
h	0.229	3.18	
j	0.71	0.864	
k	0.737	1.14	4
L	12.7	19	2
L1	-	1.27	3
L2	6.35	-	3
P	2.54	-	5
Q	-	-	6
α	45° BSC		1, 7
β	90° BSC		1

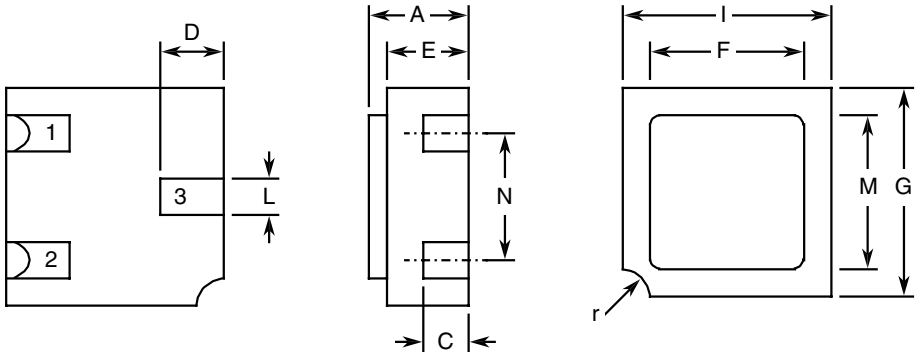
NOTES:

1. Terminal identification is specified by reference to the tab position where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
2. Applies to all leads.
3. Øb2 applies between L1 and L2. Øb applies between L1 and 12.7mm from the seating plane.

Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.

4. Measured from the maximum diameter of the actual device.
5. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
6. The details of outline in this zone are optional.
7. Measured from the Tab Centreline.

1.6.2 Chip Carrier Package (CCP) - 3 terminal

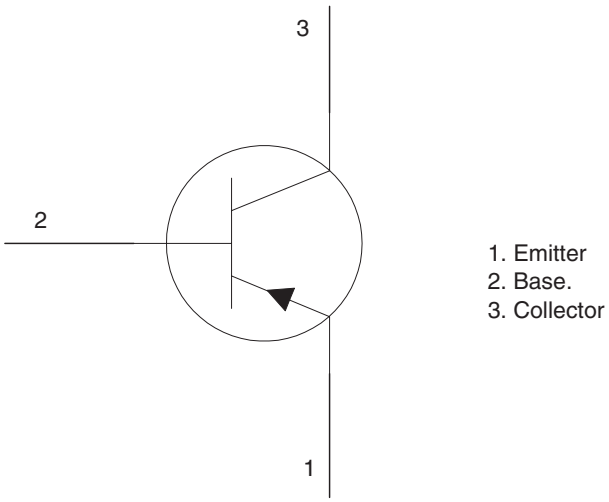


Symbols	Dimensions mm		Notes
	Min	Max	
A	1.15	1.5	
C	0.45	0.56	2
D	0.6	0.91	2
E	0.91	1.12	
F	1.9	2.15	
G	2.9	3.25	
I	2.4	2.85	
L	0.4	0.6	2
M	2.4	2.65	
N	1.8	2	
r	0.3 TYPICAL		1

NOTES:

1. Terminal identification is specified by reference to the corner notch position where terminal 1 = emitter, terminal 2 = base, terminal 3 = collector.
2. Applies to all terminals.

1.7 FUNCTIONAL DIAGRAM



NOTES:
1. For TO-39, the collector is internally connected to the case.
2. For CCP the lid is not connected to any terminal

1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case
For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.

For the chip carrier package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.

b) Leads/Terminals
As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

(a) The ESCC qualified components symbol (for ESCC qualified components only).
(b) The ESCC Component Number.
(c) Traceability information.

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-39, Test Condition: E, lead fatigue.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.4.1 Room Temperature Electrical Measurements

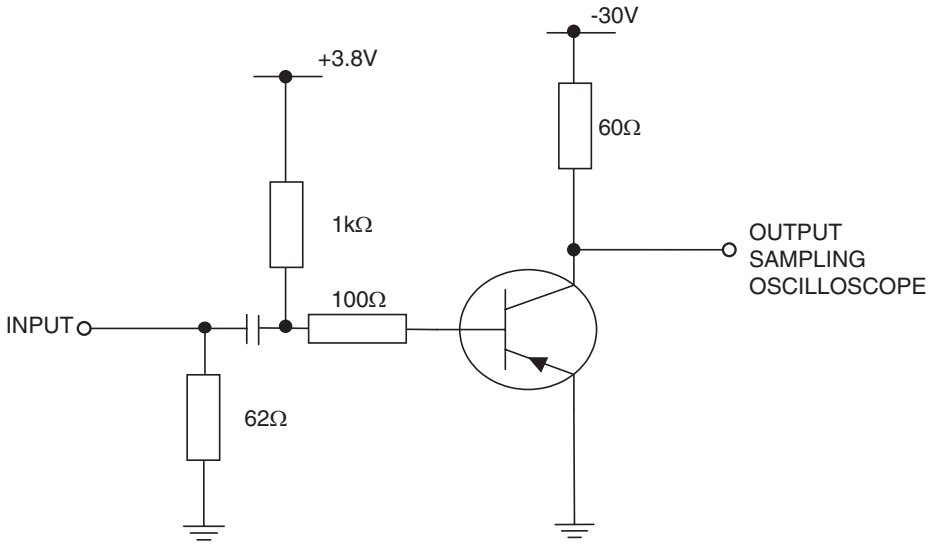
The measurements shall be performed at T_{amb}=+22 ±3°C.

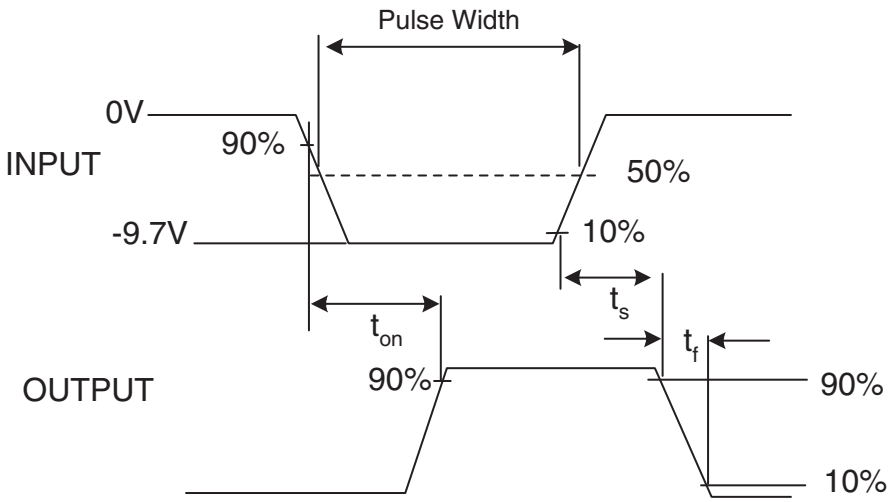
Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	I_C = -10mA Note 1 Bias condition D	-80	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	I_C = -10µA Bias condition D	-80	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	I_E = -10µA Bias condition D	-5	-	V
Collector-Emitter Cut-off Current	I_{CEX}	3041	V_{CE} = -60V, V_{BE}=2V Bias condition A	-	-25	nA
Collector-Base Cut-off Current	I_{CBO}	3036	V_{CB} = -60V Bias condition D	-	-50	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	3071	I_C=-150mA I_B=-15mA Note 1	-	-150	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	3066	I_C=-150mA I_B=-15mA Test condition A Note 1	-	-900	mV
Forward-Current Transfer Ratio	h_{FE1}	3076	V_{CE}=-5V ; I_C =-100µA	50	-	-
	h_{FE2}	3076	V_{CE}=-5V ; I_C =-100mA Note 1	100	300	-
	h_{FE3}	3076	V_{CE}=-5V ; I_C =-500mA Note 1	70	-	-
	h_{FE4}	3076	V_{CE}=-5V ; I_C =-1A Note 1	25	-	-
Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio	$\|h_{fe}\|$	3306	V_{CE}=-10V, I_C=-50mA f=100MHz Note 2	1.5	5	-
Output Capacitance	C_{obo}	3236	V_{CB}=-10V, I_E=0mA 100kHz≤f≤1MHz Note 2	-	20	pF
Turn-on Time	t_{on}	-	I_C=-500mA I_B=-50mA Notes 2, 3	-	100	ns
Storage Time	t_s	-	I_C=-500mA I_B=-50mA Notes 2, 3	-	350	ns

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Fall Time	t_f	-	I_C=-500mA I_B=-50mA Notes 2, 3	-	50	ns

NOTES:

1. Pulse measurement: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%
2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
3. t_{on}, t_s and t_f shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: Z_{OUT} = 50Ω, t_r = t_f ≤ 20ns, Pulse Width = 10±1µs, Duty Cycle ≤ 2%. The output waveform shall be monitored on an oscilloscope with the following characteristics: Z_{IN} ≥ 100kΩ, C_{IN} ≤ 12pF, t_r ≤ 10ns.





2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Collector-Base Cut-off Current	I_{CBO}	3036	T_{amb}=+150 (+0 -5)°C V_{CB}=-60V Bias condition D	-	-50	µA
Forward-Current Transfer Ratio 3	h_{FE3}	3076	T_{amb}=-55 (+5 -0)°C V_{CE}=-5V I_C=-500mA Note 2	30	-	–

NOTES:
1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
2. Pulse measurement: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb}=+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Collector-Base Cut-off Current	I_{CBO}	±10 or (1) ±100%	-	-50	nA
Forward-Current Transfer Ratio 2	h_{FE2}	±25%	100	300	-

NOTES:
1. Whichever is the greater referred to initial value.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb}=+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Base Cut-off Current	I_{CBO}	-	-50	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-150	mV
Forward-Current Transfer Ratio 2	h_{FE2}	100	300	-

2.7 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150(+0 -5)	^{o}C
Emitter-Base Voltage	V_{EB}	4	V
Collector-Base Voltage	V_{CB}	40	V
Duration	t	48 minimum	hours

2.8 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+20 to +50	^{o}C
Power Dissipation	P_{tot}	As per Maximum Ratings P_{tot1} derated at the chosen T_{amb}	W
Collector-Base Voltage	V_{CB}	-40	V

2.9 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Production Control-Chart F2	Special In-process Control Internal Visual Inspection. For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 0076637.
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.